

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Prior Application: S. HANZAWA et al
Serial No. 10/357,222
Filed: February 4, 2003

Group Art: 2818
Examiner: T.Q. Le
For: SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450


December 4, 2003

Sir:

In accordance with the duty of disclosure, the Applicants inform the Examiner of the documents cited during prosecution of the parent application, USSN 10/357,222.

The Applicants request that the Examiner initial and return a copy of the attached PTO-1449 form as an indication that the references have been considered.

Respectfully submitted,


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FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. ASA-1022-03		SERIAL NO.	
LIST OF DOCUMENTS CITED BY APPLICANT <i>(Use several sheets if necessary)</i>				APPLICANT S. HANZAWA et al			
				FILING DATE 12/04/03		GROUP 2818	
U.S. PATENT DOCUMENTS							
* EXAMINER INITIAL	DOCUMENT	DATE	NAME	CLASS	SUBCLASS	FILING DATE <i>(If Appropriate)</i>	
AA	5,793,697	08/11/98	Scheuerlein				
AB	6,314,014	11/06/01	Lowrey et al				
AC	5,258,958	11/1993	Iwahashi et al				
AD	5,226,014	07/1993	McManus				
AE	5,410,509	04/1995	Morita				
AF	5,508,960	04/1996	Pinkham				
AG	4,758,995	07/1988	Sato				
AH							
AI							
AJ							
AK							
FOREIGN PATENT DOCUMENTS							
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO	
AL						<input type="checkbox"/>	<input type="checkbox"/>
AM						<input type="checkbox"/>	<input type="checkbox"/>
AN						<input type="checkbox"/>	<input type="checkbox"/>
AO						<input type="checkbox"/>	<input type="checkbox"/>
AP						<input type="checkbox"/>	<input type="checkbox"/>
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, etc.)</i>							
	AR	Scheuerlein, R., et al, "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", IEEE					
		International Solid-State Circuits Conference, DIGEST OF TECHNICAL PAPERS, Feb 8, 2000, pp 128-131.					
	AS	U.S. Patent Application Publication No. US 2001/0053104,					
		Published Dec 20, 2001, Tran et al.					
	AT						
EXAMINER				DATE CONSIDERED			
<small>* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							